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Kind regards,

Team Nexperia



# **2PB709ART** 45 V, 100 mA PNP general-purpose transistor Rev. 01 — 19 March 2007

**Product data sheet** 

# 1. Product profile

### 1.1 General description

PNP general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: 2PD601ART.

### **1.2 Features**

- General-purpose transistor
- Small SMD plastic package

### 1.3 Applications

General-purpose switching and amplification

### **1.4 Quick reference data**

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-45	V
l <sub>C</sub>	collector current		-	-	-100	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -2 mA	210	-	340	

# 2. Pinning information

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter		3
3	collector		
			sym013



### 45 V, 100 mA PNP general-purpose transistor

### 3. Ordering information

Table 3. Order	Ordering information					
Type number	Package					
	Name	Description	Version			
2PB709ART	-	plastic surface-mounted package; 3 leads	SOT23			

### 4. Marking

Table 4. Ma	rking codes	
Type number	М	larking code <sup>[1]</sup>
2PB709ART	C	5*
21 87 007 411		

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

### 5. Limiting values

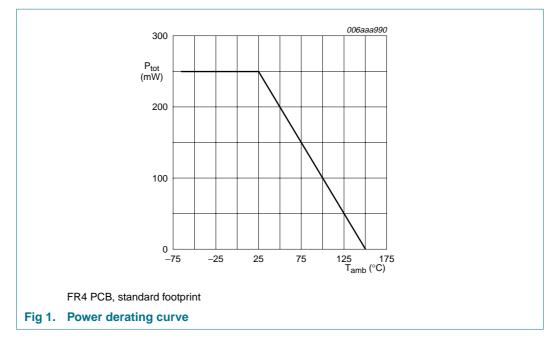
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{array}{cccc} V_{CBO} & \mbox{collector-base voltage} & \mbox{open emitter} & - & -45 & V \\ \hline V_{CEO} & \mbox{collector-emitter voltage} & \mbox{open base} & - & -45 & V \\ \hline V_{EBO} & \mbox{emitter-base voltage} & \mbox{open collector} & - & -6 & V \\ \hline I_C & \mbox{collector current} & \mbox{single pulse;} & - & -100 & \mbox{mA} \\ \hline I_{CM} & \mbox{peak collector current} & \mbox{single pulse;} & - & -200 & \mbox{mA} \\ \hline I_{BM} & \mbox{peak base current} & \mbox{single pulse;} & - & -100 & \mbox{mA} \\ \hline I_{bm} & \mbox{peak base current} & \mbox{single pulse;} & - & -100 & \mbox{mA} \\ \hline I_{t_p} \leq 1 \ \mbox{ms} & \mbox$	Symbol	Parameter	Conditions	Min	Max	Unit
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V <sub>CBO</sub>	collector-base voltage	open emitter	-	-45	V
I_LBCcollector current100mAI_Ccollector currentsingle pulse; $t_p \le 1 \text{ ms}$ 200mAI_BMpeak base currentsingle pulse; $t_p \le 1 \text{ ms}$ 100mAP_tottotal power dissipationT_amb $\le 25 \text{ °C}$ 11-250mWTjjunction temperature-150°CT_ambambient temperature-65+150°C	V <sub>CEO</sub>	collector-emitter voltage	open base	-	-45	V
$      I_{CM} \qquad \mbox{peak collector current} \qquad \mbox{single pulse;} \\ t_p \le 1 \mbox{ ms} \qquad \mbox{-} 200 \qquad \mbox{mA} \\      I_{BM} \qquad \mbox{peak base current} \qquad \mbox{single pulse;} \\ t_p \le 1 \mbox{ ms} \qquad \mbox{-} -100 \qquad \mbox{mA} \\      P_{tot} \qquad \mbox{total power dissipation} \qquad \mbox{T}_{amb} \le 25 \ ^{\circ}\text{C} \qquad \mbox{11} \ \mbox{-} 250 \qquad \mbox{mW} \\      T_j \qquad \mbox{junction temperature} \qquad \mbox{-} 150  \ \ ^{\circ}\text{C} \\      T_{amb} \qquad \mbox{ambient temperature} \qquad \mbox{-} 65 \qquad \mbox{+} 150  \ ^{\circ}\text{C} \\            $	V <sub>EBO</sub>	emitter-base voltage	open collector	-	-6	V
$t_p \le 1 \text{ ms}$ $I_{BM}$ peak base currentsingle pulse; $t_p \le 1 \text{ ms}$ 100mA $P_{tot}$ total power dissipation $T_{amb} \le 25 \text{ °C}$ [1]-250mW $T_j$ junction temperature-150°C $T_{amb}$ ambient temperature-65+150°C	I <sub>C</sub>	collector current		-	-100	mA
$\label{eq:total_power_dissipation} t_p \leq 1 \text{ ms}$ $P_{tot}  total power dissipation  T_{amb} \leq 25 \ ^{\circ}\text{C} \qquad \begin{tabular}{lllllllllllllllllllllllllllllllllll$	I <sub>CM</sub>	peak collector current	• •	-	-200	mA
T_jjunction temperature-150°CT_{amb}ambient temperature-65+150°C	I <sub>BM</sub>	peak base current	• •	-	-100	mA
$T_{amb}$ ambient temperature $-65 +150$ °C	P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	250	mW
	Tj	junction temperature		-	150	°C
$T_{stg}$ storage temperature -65 +150 °C	T <sub>amb</sub>	ambient temperature		-65	+150	°C
•	T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 45 V, 100 mA PNP general-purpose transistor



# 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	140	K/W

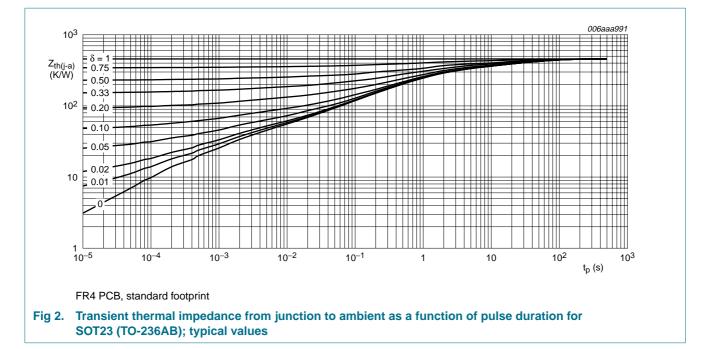
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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#### 45 V, 100 mA PNP general-purpose transistor



### 7. Characteristics

#### Table 7.Characteristics

 $T_{amb} = 25 \circ C$  unless otherwise specified.

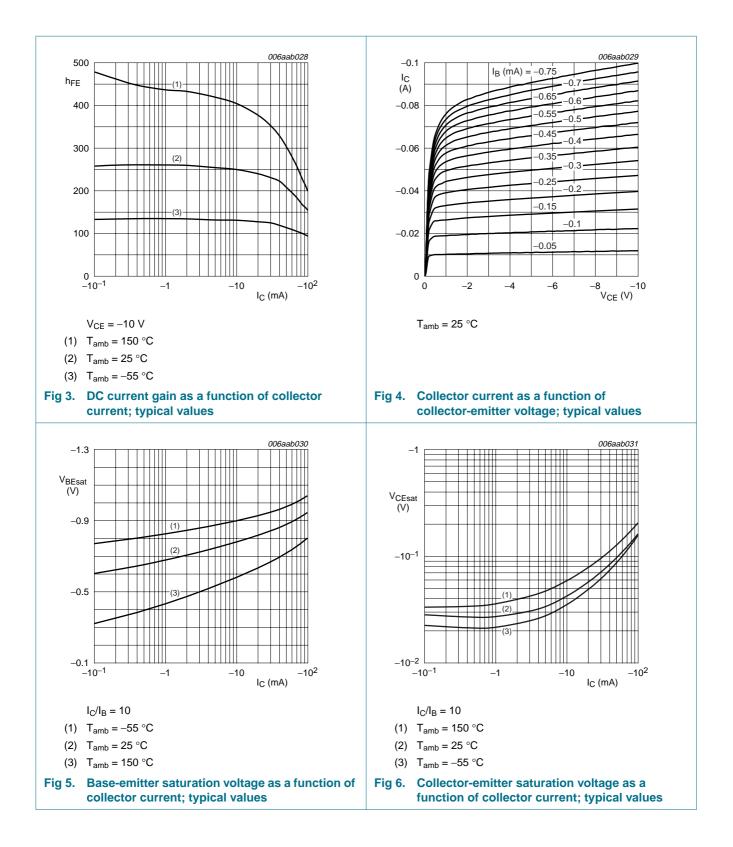
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -45 \text{ V}; \text{ I}_{\text{E}} = 0 \text{ A}$		-	-	-10	nA
	current	$V_{CB} = -45 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-10	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V};$ $I_C = -2 \text{ mA}$		210	-	340	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C} = -100 \text{ mA};$ $I_{\rm B} = -10 \text{ mA}$	<u>[1]</u>	-	-	-500	mV
f <sub>T</sub>	transition frequency	$V_{CE} = -10 V;$ $I_{C} = -1 mA;$ f = 100 MHz		70	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 V;$ $I_E = i_e = 0 A;$ f = 1 MHz		-	-	5	pF

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .

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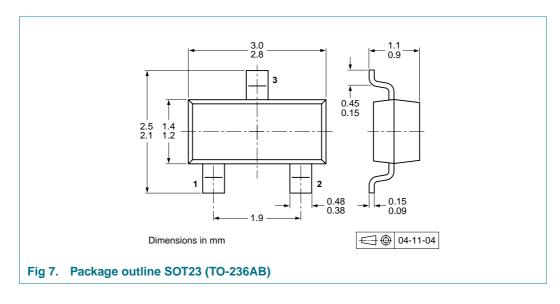
# **2PB709ART**

#### 45 V, 100 mA PNP general-purpose transistor



45 V, 100 mA PNP general-purpose transistor

### 8. Package outline



# 9. Packing information

#### Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity
			3000	10000
2PB709ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

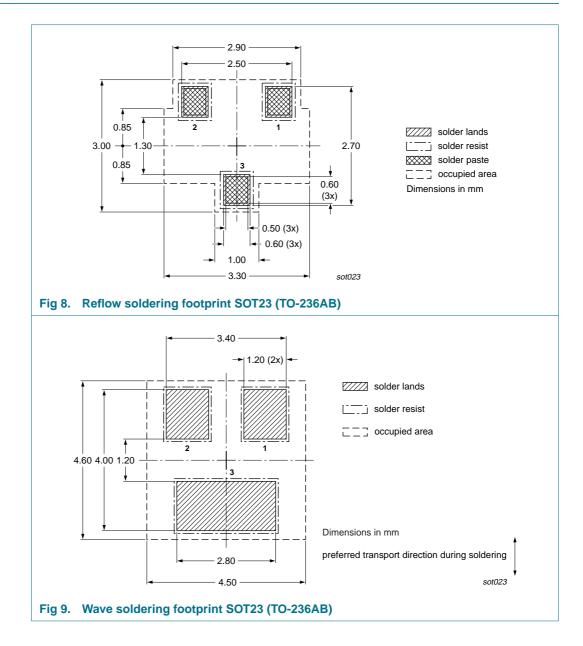
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

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# **10. Soldering**



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### 45 V, 100 mA PNP general-purpose transistor

# **11. Revision history**

Table 9. Revision his	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
2PB709ART_1	20070319	Product data sheet	-	-			

#### 45 V, 100 mA PNP general-purpose transistor

## **12. Legal information**

### **12.1 Data sheet status**

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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